

**N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**
**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	5Ω @ V <sub>GS</sub> = 10V	210mA
	7.5Ω @ V <sub>GS</sub> = 5V	170mA

**Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Notes 3)**
- **The 2N7002Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

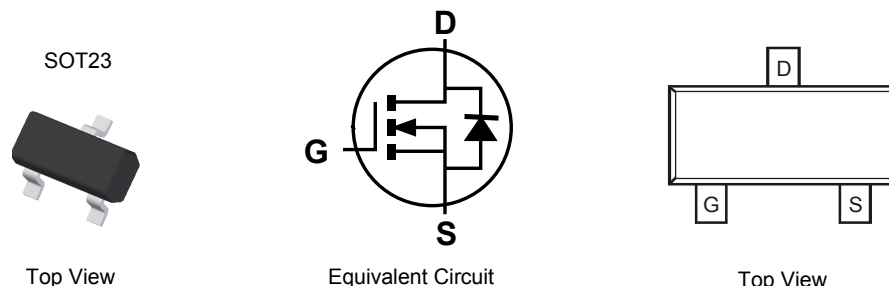
**Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions

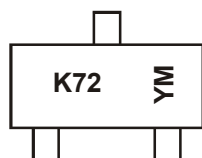
**Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 <sup>(e3)</sup>
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)


**Ordering Information** (Note 4)

Part Number	Case	Packaging
2N7002Q-7-F	SOT23	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**


K72 = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: I = 2021)  
 M = Month (ex: 9 = September)

**Date Code Key**

Year	2002	.....	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	N	.....	I	J	K	L	M	N	O	P	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0\text{M}\Omega$			$V_{DGR}$	60	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
				$\pm 40$	
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	170	mA
		$T_A = +85^\circ\text{C}$		120	
		$T_A = +100^\circ\text{C}$		105	
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	210	mA
		$T_A = +85^\circ\text{C}$		150	
		$T_A = +100^\circ\text{C}$		135	
Maximum Continuous Body Diode Forward Current (Note 6)			$I_S$	0.2	A
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)				800	

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 5)	$P_D$	370	mW
	(Note 6)		540	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	348	$^\circ\text{C/W}$
	(Note 6)		241	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	91	
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	70	—	V	$V_{GS} = 0\text{V}, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1.0 500	$\mu\text{A}$	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$ @ $T_J = +25^\circ\text{C}$ @ $T_J = +125^\circ\text{C}$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 10$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.2 2.4 4.4	7.5 5.0 13.5	$\Omega$	$V_{GS} = 5.0\text{V}, I_D = 0.05\text{A}$ @ $T_J = +25^\circ\text{C}$ @ $T_J = +25^\circ\text{C}$ @ $T_J = +125^\circ\text{C}$ $V_{GS} = 10\text{V}, I_D = 0.5\text{A}$ $V_{GS} = 10\text{V}, I_D = 0.5\text{A}$
On-State Drain Current	$I_{D(ON)}$	0.5	1.0	—	A	$V_{GS} = 10\text{V}, V_{DS} = 7.5\text{V}$
Forward Transconductance	$g_{FS}$	80	—	—	mS	$V_{DS} = 10\text{V}, I_D = 0.2\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.78	1.5	V	$V_{GS} = 0\text{V}, I_S = 115\text{mA}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{ISS}$	—	22	50	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{OSS}$	—	11	25	pF	
Reverse Transfer Capacitance	$C_{RSS}$	—	2.0	5.0	pF	
Gate Resistance	$R_g$	—	120	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V},$ $f = 1.0\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_g$	—	223	—	pC	$V_{DS} = 10\text{V}, I_D = 250\text{mA}$
Gate-Source Charge	$Q_{GS}$	—	82	—		
Gate-Drain Charge	$Q_{GD}$	—	178	—		
Turn-On Delay Time	$t_{D(ON)}$	—	2.8	—	ns	$V_{DD} = 30\text{V}, I_D = 0.2\text{A},$ $R_L = 150\Omega, V_{GEN} = 10\text{V},$ $R_{GEN} = 25\Omega$
Turn-On Rise Time	$t_R$	—	3.0	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	7.6	—		
Turn-Off Fall Time	$t_F$	—	5.6	—		

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

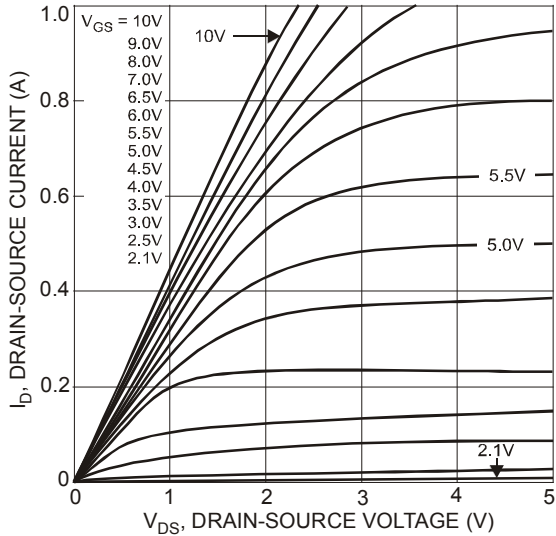


Fig. 1 On-Region Characteristics

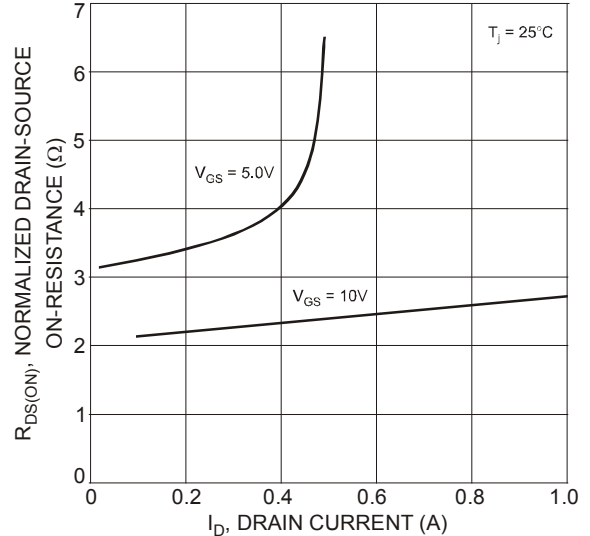


Fig. 2 On-Resistance vs. Drain Current

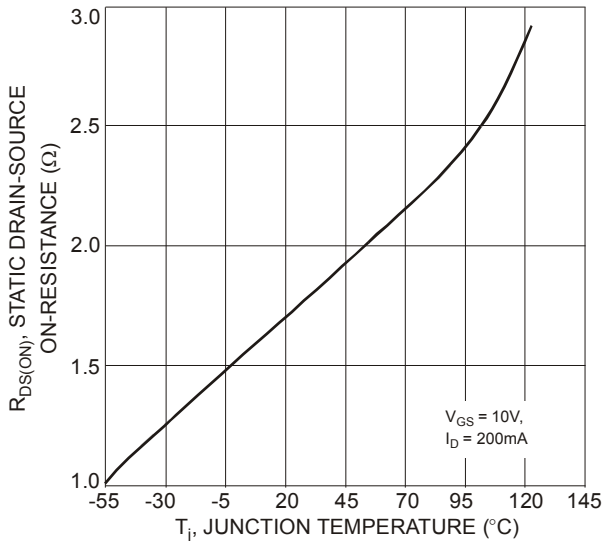


Fig. 3 On-Resistance vs. Junction Temperature

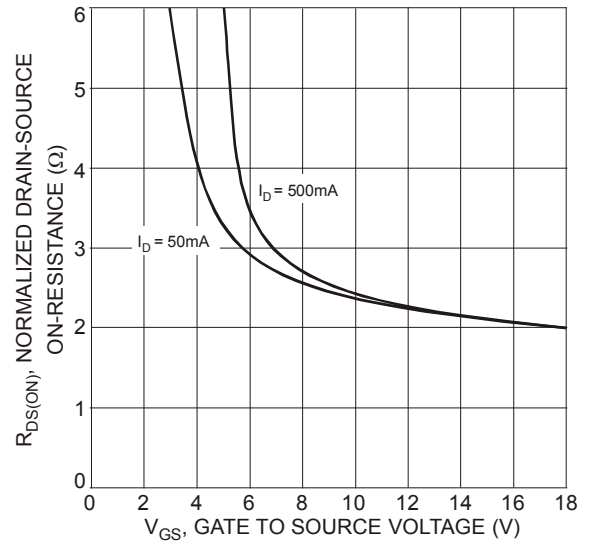


Fig. 4 On-Resistance vs. Gate-Source Voltage

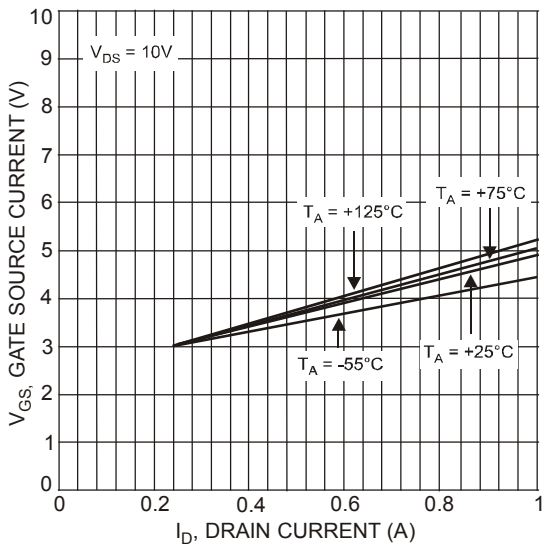


Fig. 5 Typical Transfer Characteristics

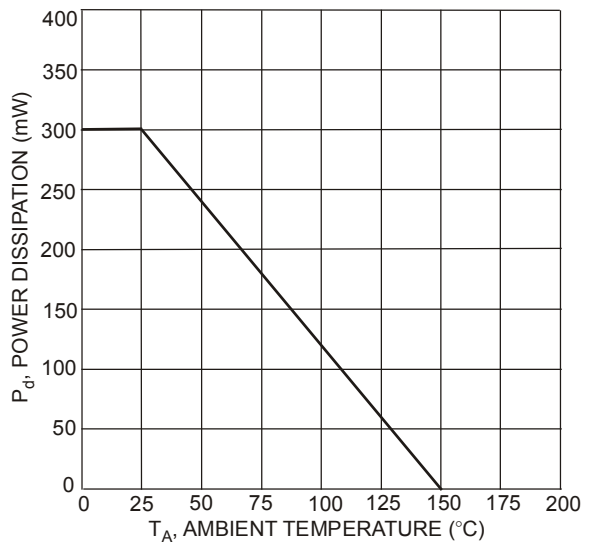
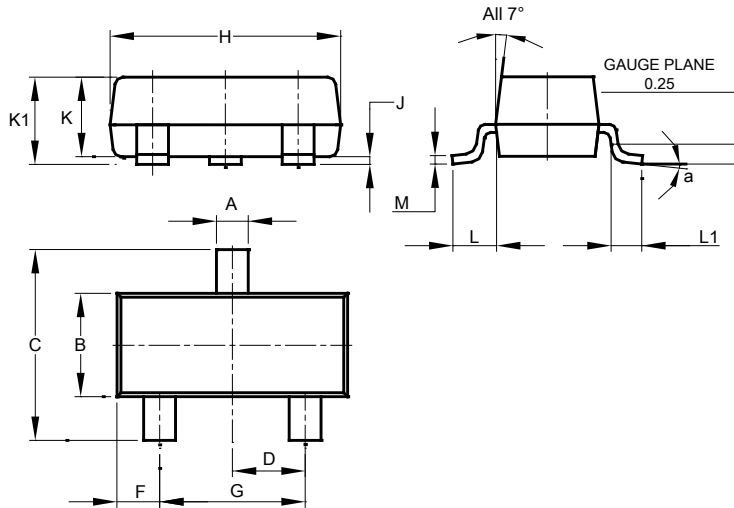


Fig. 6 Max Power Dissipation vs. Ambient Temperature

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**

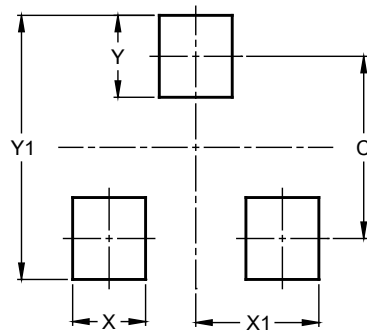


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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